Abstracts

Super Low Noise Packaged GaAs FETs for Ku Band

T. Suzuki, M. Ito, A. Nara, Y. Kadowaki and M. Nakatani. "Super Low Noise Packaged GaAs FETs for Ku Band." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 367-369.

By selecting a high quality GaAs epitaxial wafer and reducing parasitics, packaged FETs with NF/sub min/ of 2.4 dB and G/sub a/ of 7.5 dB at 18 GHz were produced. Using these FETs, a single stage amplifler with NF of 2.7 dB and G of 6.4 dB at 18 GHz was constructed.

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